

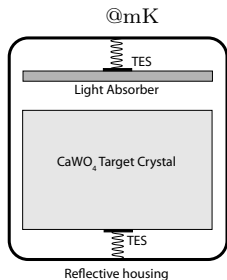
Neganov-Luke Amplified Cryogenic Light-Detectors: Current Status and Future Applications

HAP Workshop on Advanced Technologies
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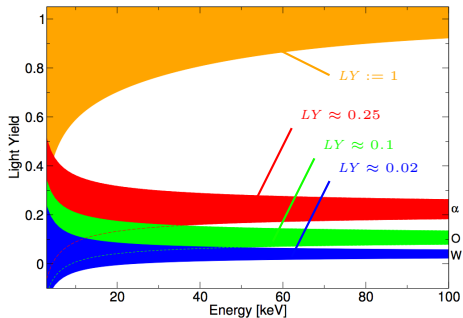
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Cryogenic Light Detectors (CRESST & EURECA)

- ▶ **Cryogenic light detector:** Semiconductor absorber operated at cryogenic Temperatures ($\mathcal{O}(\text{mK})$), thermal signal read-out with thermometer (**TES**, NTD, MMC)
- ▶ Absorber materials: **Si**, Ge, SOS (Silicon on Sapphire)
- ▶ Good radiopurity (& active detector), large area
- Background suppression in rare event search experiments by detecting phonon & light signal!
- Separation of signal and background evts. via Light Yield

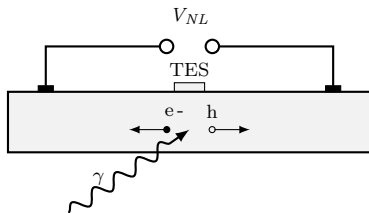


$$LY = \frac{E_{light}}{E_{CaWO_4}}$$



Neganov-Luke Effect

Amplification of thermal signal by drifting electrons & holes in a semiconductor absorber in an applied electric field [1].

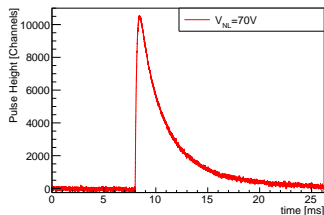
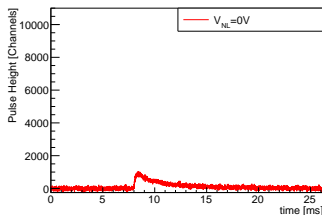


$$E_{tot} = G_{th} \cdot E = \left(1 + \frac{eV_{NL}}{\epsilon} \right) \cdot E$$

$$\epsilon = E_{ph}/\eta$$

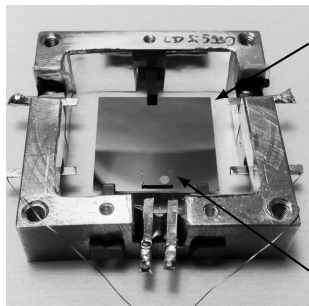
(Energy required to create e-h pair)

→ Signal amplification **and** improvement in S/N ratio!



Fabrication

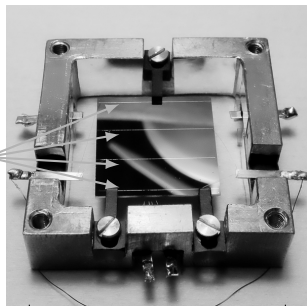
- ▶ High-purity p-type Silicon ($\rho > 10 \text{ k}\Omega$) absorber (here: $20 \times 20 \times 0.5 \text{ mm}$).
- ▶ Aluminum strips (electrodes) produced via photolithographic lift-off process. (Application of photoresist (PR), baking, UV exposure, developing of PR, deposition of Al, removal of PR & cleaning of substrate)
- ▶ Natural oxide layer removed by Ar-etching, Al deposited via EBE or sputtering.
- ▶ Substrate + contacts annealed in forming gas.
- ▶ TES carrier glued to substrate (EpoTek 301-2).
- ▶ TES & Al strips contacted by wire bonding ($25\mu\text{m}$ Al).



Si absorber

Al contacts

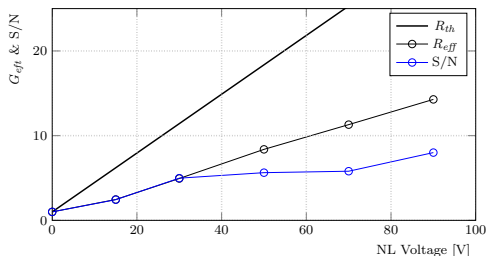
TES



40mm

Challenges

Amplification (G_{th}) lower than predicted



→ Reduced drift length: charge carriers trapped before reaching electrodes

$$G_{eff} = 1 + \frac{e \cdot V_{NL}}{\epsilon} \cdot \frac{l}{d}$$

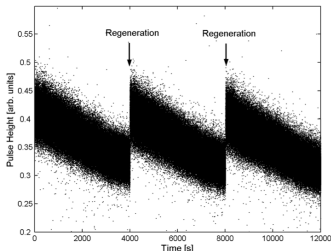
→ Trapping in impurities / defects close to the absorber surface.

→ Achieved amplification varies between devices!

⇒ Possible solution: production process without photolithographic step.
(Structuring with shadow mask currently under investigation)

Challenges

Amplification reduced over time



Initially [2]:
Drift: 20% in $\sim 1\text{h}$
(@ 50keV/s)

- Charge carriers trapped (accumulate) near / below aluminum contacts.
- effective electric field is reduced:

$$V_{NL} \rightarrow V_{eff,NL}(t)$$

Regular regeneration necessary!

(turn off V_{NL} , flush detector with light, turn on V_{NL})

- ⇒ **Behavior improved by annealing of substrate / contacts!**
Healing of defects induced during manufacturing.
(Greatly reduced drift / no drift (currently under investigation))

Challenges

Amplification reduced over time

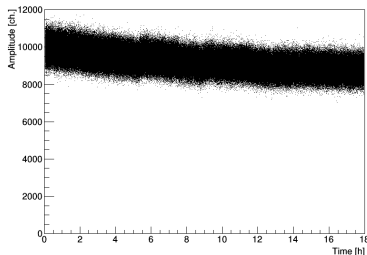
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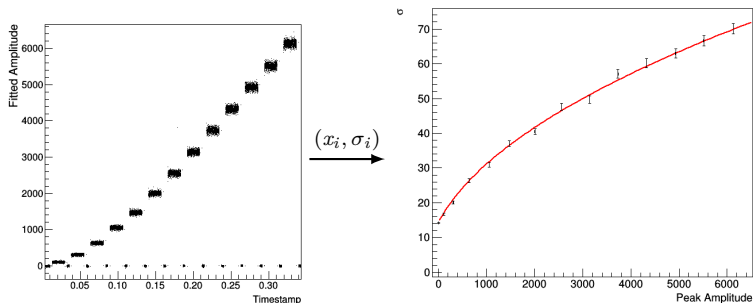


Now:

Drift: 10% in 18h
(@ 50keV/s)

Calibration ($V_{NL} = 0$ V)

- Calibration via “LED Calibration Technique”
(LED mounted outside of cryostat @ room temperature)
- ▶ Detector illuminated by light-pulses of variable intensity.
(λ_{LED} can be chosen to match e.g. scintillation light of crystal.)



- ▶ Calibration function (lin. response $x = a \cdot N$ & photon stat. $\sigma_{ph} = a \cdot \sqrt{N}$):

$$\sigma_{tot}^2 = \sigma_{ph}^2 + \sigma_{el}^2 + \sigma_{tr}^2 + \sigma_{pos}^2 + \dots = \sigma_0^2 + \sigma_{ph}^2 \rightarrow \sigma_{tot} = \sqrt{\sigma_0^2 + a \cdot x}$$

- ⇒ **Scaling factor a & threshold σ_0 (here: $\sigma_0 \approx 50$ eV)**

Calibration (with applied V_{NL})

In ideal case: signal is amplified $x_{NL} = A \cdot x$.

$$\rightarrow \sigma_{tot,ideal} = \sqrt{\sigma_0^2 + a \cdot A \cdot x}$$

⇒ ideal calibration function does not describe data!

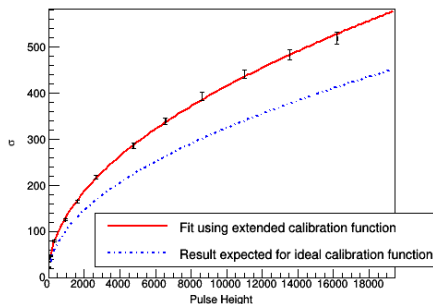
⇒ Extended calibration function [3]:

$$\sigma_{tot} = \sqrt{\sigma_0^2 + \sigma_{NL}^2 + a \cdot A \cdot x + b \cdot x + c \cdot x^2}$$

$\sigma_{cc} = \sqrt{b(V_{NL}) \cdot x} \propto \sqrt{N}$: accounts for incomplete charge collection (trapping)

$\sigma_{rc} = \sqrt{c(V_{NL}) \cdot x^2} \propto N$: accounts for possible recombination of charge carriers.

⇒ Fitting new model to data → good agreement! (here: $\sigma_0 + \sigma_{NL} \approx 9 \text{ eV}$)



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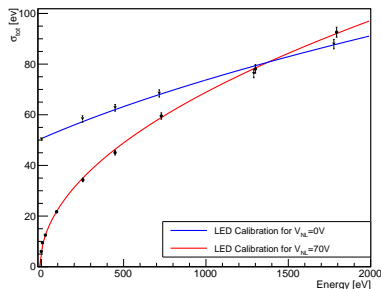
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→ Improvement in resolution below $\sim 1 \text{ keV}$ light energy!

$1 \text{ keV} \approx 70 \text{ keV } e^-$ - recoil

$\approx 700 \text{ keV O}$ - recoil

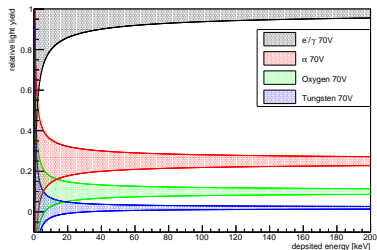
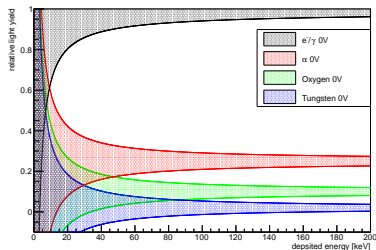
$\approx 3.5 \text{ MeV W}$ - recoil

⇒ **Improvement in energy range relevant for DM search.**
(Current performance comparable to detectors used in CRESST)

Applications

Improvement of background suppression in CaWO_4

- Improved separation of e^-/γ and nuclear recoils possible.
- Improved separation of between different nuclear recoils possible.



(calculated 80% LY bands for detector shown on prev. slide)

- ⇒ Next step: test NL detectors in realistic low-background environment.

Applications

Detectors initially developed for DM search, but other applications possible:

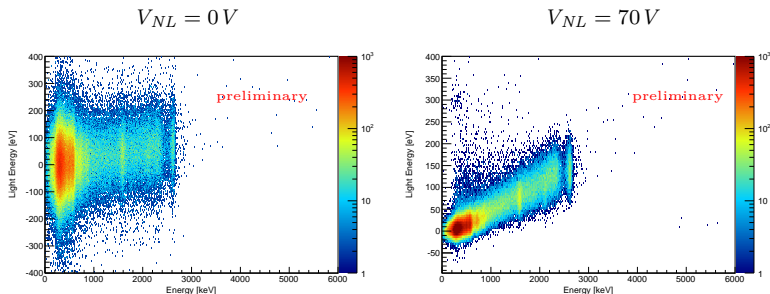
Background suppression in $0\nu\beta\beta$ experiments using TeO_2

(or other non-scintillating crystals.)

→ Suppression of e^-/γ from α events via Cherenkov light.

@ $Q_{\beta\beta}(^{130}\text{Te}) (= 2.53 \text{ MeV})$: $\approx 450 \text{ eV}$ emitted in Cherenkov light!

Cherenkov threshold: $\sim 50 \text{ keV}$ for e^- and $\sim 400 \text{ MeV}$ for α



Conclusion & Outlook

- ▶ Improvement of resolution in energy range relevant for rare event searches.
- ▶ Neganov-Luke amplified cryogenic light-detectors have great potential to further improve the background suppression in cryogenic rare event searches. (CRESST, EURECA & possible future $0\nu\beta\beta$ experiments)
- ▶ Reduced overall-amplification currently under investigation.
- ▶ Great improvements concerning the reduction of G_{eft} over time achieved.
- further room for improvement → under investigation.
- Goal: no regeneration necessary!
- ▶ New calibration function to described behavior with applied V_{NL}

-
- ⇒ Next step: Further investigation of improved production process & annealing.
 - ⇒ Next step: Test NL detectors in realistic low-background environment.

Acknowledgments

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Thank you for your attention!

References

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- [3] S. Roth, The Potential of Neganov-Luke Amplified Cryogenic Light Detectors and the Scintillation-Light Quenching Mechanism in CaWO₄ Single Crystals in the Context of the Dark Matter Search Experiment CRESST-II.
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